Oddělení diodově čerpaných laserů a realizační tým projektu HiLASE
Vás zve na seminář

Development of the 1st generation laser-produced plasma source for EUV lithography

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We report on latest status of the 1st generation laser-produced plasma source system ("ETS" device) for EUV lithography. The device consists of the original concepts: (1) CO_2 laser driven plasma, (2) hybrid CO_2 laser system that is combination of high speed (>100 kHz) short pulse oscillator and industrial cw-CO_2 laser, (3) magnetic mitigation, and (4) double pulse EUV plasma creation. Maximum burst on time power is 104 W (100 kHz, 1.0 mJ EUV power @ intermediate focus), laser-EUV conversion efficiency is 2.5 %, duty cycle is 20 % at maximum. Continuous operation time is so far up to an hour.

který se bude konat dne 19.11. 2010 od 10:00 v zasedacím sále Fyzikálního ústavu AV ČR, v.v.i.